

CLEAN COPY OF THE AMENDED CLAIMS

1(Amended). A method of producing a semiconductor device, comprising the step of:
dry etching an upper layer pattern of an insulating film in a state where at least a part of
the insulating film formed above an element separation and a substrate is exposed; and
exposing a surface of the insulating film to a film formation atmosphere of the insulating
film prior to forming additional layers upon the insulating film after the dry etching.

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